L Number	Hits	Search Text	DB	Time stamp
1	0	(gate adj array) and (esd adj implantation)	USPAT; US-PGPUB; EPO; JPO;	2004/04/12 15:53
2	0	(gate adj array) and (esd adj diffusion)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/12 15:53
3	4	esd adj diffusion	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/12 15:55
4	52	esd adj implant	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/12 16:04
5	0	surge adj protection adj (implant or implantaion or diffusion or dopant)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/12 16:05
6	65	(esd or (electrostatic adj discharge)) adj (implant or implantaion or diffusion or dopant)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/12 16:19
7	1	(voltage adj protection) adj (implant or implantaion or diffusion or dopant)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/12 17:02
8	2	20020076876.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/12 17:04
9	2	6008080.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/12 18:18
10	2	6268256.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/04/12 18:18
-	2	5559352.pn.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/07 18:17
-	2	20030141551.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/07
-	0	(esd adj (layer or region or film)) adj drain	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/07
-	0	((electro adj static adj discharge) adj (layer or region or film)) adj drain	DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/07 18:40

Search History 4/12/04 7:26:54 PM

_	0	((electrostatic adj discharge) adj (layer or region or film)) adj drain	USPAT; US-PGPUB;	2004/04/07 18:40
			EPO; JPO; DERWENT; IBM TDB	
_	0	((breakdown adj enhanced) adj (layer or region or film)) adj drain	USPAT; US-PGPUB;	2004/04/07
		region of film), and drain	EPO; JPO;	10.40
			DERWENT; IBM TDB	i
-	3	(esd adj (layer or region or film)) near	USPAT; US-PGPUB;	2004/04/07 18:41
			EPO; JPO;	10.11
			DERWENT; IBM_TDB	
-	0	((electro adj static adj discharge) adj (layer or region or film)) near drain	USPAT; US-PGPUB;	2004/04/07 18:41
			EPO; JPO; DERWENT;	
			IBM_TDB	0004/04/05
-	0	((electrostatic adj discharge) adj (layer or region or film)) near drain	USPAT; US-PGPUB;	2004/04/07 18:42
			EPO; JPO; DERWENT;	
_		((breakdown adj enhanced) adj (layer or	IBM_TDB USPAT;	2004/04/07
		region or film)) near drain	US-PGPUB;	18:42
			EPO; JPO; DERWENT;	
_	34	(esd adj (layer or region or film)) with	IBM_TDB USPAT;	2004/04/07
		drain	US-PGPUB; EPO; JPO;	18:46
			DERWENT;	
_	0	((electro adj static adj discharge) adj	IBM_TDB USPAT;	2004/04/07
		(layer or region or film)) with drain	US-PGPUB; EPO; JPO;	18:50
			DERWENT; IBM TDB	
-	2	((electrostatic adj discharge) adj (layer or region or film)) with drain	USPAT; US-PGPUB;	2004/04/07 18:47
		or region of rim,, with drain	EPO; JPO;	10.47
			DERWENT; IBM_TDB	
-	2	((breakdown adj enhanced) adj (layer or region or film)) with drain	USPAT; US-PGPUB;	2004/04/07 18:47
			EPO; JPO; DERWENT;	
_	29	(esd adj (layer or region or film)) with	IBM_TDB USPAT;	2004/04/07
		source	US-PGPUB;	18:46
			EPO; JPO; DERWENT;	
_	0	((electro adj static adj discharge) adj	<pre>IBM_TDB USPAT;</pre>	2004/04/07
		(layer or region or film)) with source	US-PGPUB; EPO; JPO;	18:47
			DERWENT; IBM TDB	
-	3		USPĀT;	2004/04/07
		or region or film)) with source	US-PGPUB; EPO; JPO;	18:47
		·	DERWENT; IBM_TDB	
-	1	((breakdown adj enhanced) adj (layer or region or film)) with source	USPĀT; US-PGPUB;	2004/04/07 18:47
			EPO; JPO; DERWENT;	
			IBM TDB	

-	61	(USPAT;	2004/04/07
,		esd or (electrostatic adj discharge) or	US-PGPUB;	19:02
		breakdown or enhance) near2 formed near2	EPO; JPO;	
	1	(source or drain)	DERWENT;	
	1		IBM TDB	
-	76	((breakdown or enhance) adj (layer or	USPAT;	2004/04/07
	1	film or region)) and esd	US-PGPUB;	19:03
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
i -	79	((breakdown or enhanced) adj (layer or	USPAT;	2004/04/07
		film or region)) and esd	US-PGPUB;	19:04
		1	EPO; JPO;	
			DERWENT;	
ļ			IBM TDB	
-	877	(body adj region) and (drift)	USPAT;	2004/04/07
			US-PGPUB;	19:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2471	(breakdown or enhanced) adj (layer or	USPAT;	2004/04/07
		film or region)	US-PGPUB;	19:09
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	10	(reduce adj breakdown adj voltage) with	USPĀT;	2004/04/07
ļ		drain with esd	US-PGPUB;	19:56
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	35	esd adj implantation	USPAT;	2004/04/12
			US-PGPUB;	15:52
			EPO; JPO;	
			DERWENT;	
			IBM TDB	